

IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors

1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 plastic package. This very sensitive gate "series D" triac is intended for interfacing with low power drivers including microcontrollers.

2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing with low power gate drivers and microcontrollers
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Very sensitive gate
- Triggering in all four quadrants

3. Applications

- Air conditioner indoor fan control
- General purpose low power motor control
- General purpose switching and phase control

4. Quick reference data

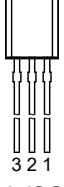
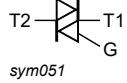
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 51^\circ\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25^\circ\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	12.5	A
		full sine wave; $T_{j(init)} = 25^\circ\text{C}$; $t_p = 16.7\text{ ms}$	-	-	13.7	A
T_j	junction temperature		-	-	125	$^\circ\text{C}$
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25^\circ\text{C}$; Fig. 7	-	-	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25^\circ\text{C}$; Fig. 7	-	-	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25^\circ\text{C}$; Fig. 7	-	-	5	mA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		$V_D = 12 \text{ V}$; $I_T = 0.1 \text{ A}$; T2- G+; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 7		-	-	7	mA
I_H	holding current	$V_D = 12 \text{ V}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 9		-	1.3	10	mA
V_T	on-state voltage	$I_T = 1.4 \text{ A}$; $T_j = 25 \text{ }^\circ\text{C}$; Fig. 10		-	1.2	1.5	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402 \text{ V}$; $T_j = 125 \text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; $R_{GT1(ext)} = 1 \text{ k}\Omega$		20	-	-	V/ μ s
dV_{com}/dt	rate of change of commutating voltage	$V_D = 400 \text{ V}$; $T_j = 125 \text{ }^\circ\text{C}$; $dl_{com}/dt = 0.5 \text{ A/ms}$; $I_T = 1 \text{ A}$; gate open circuit		3	-	-	V/ μ s

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		
2	G	gate		
3	T1	main terminal 1	 TO-92 (SOT54)	 sym051

6. Ordering information

Table 3. Ordering information

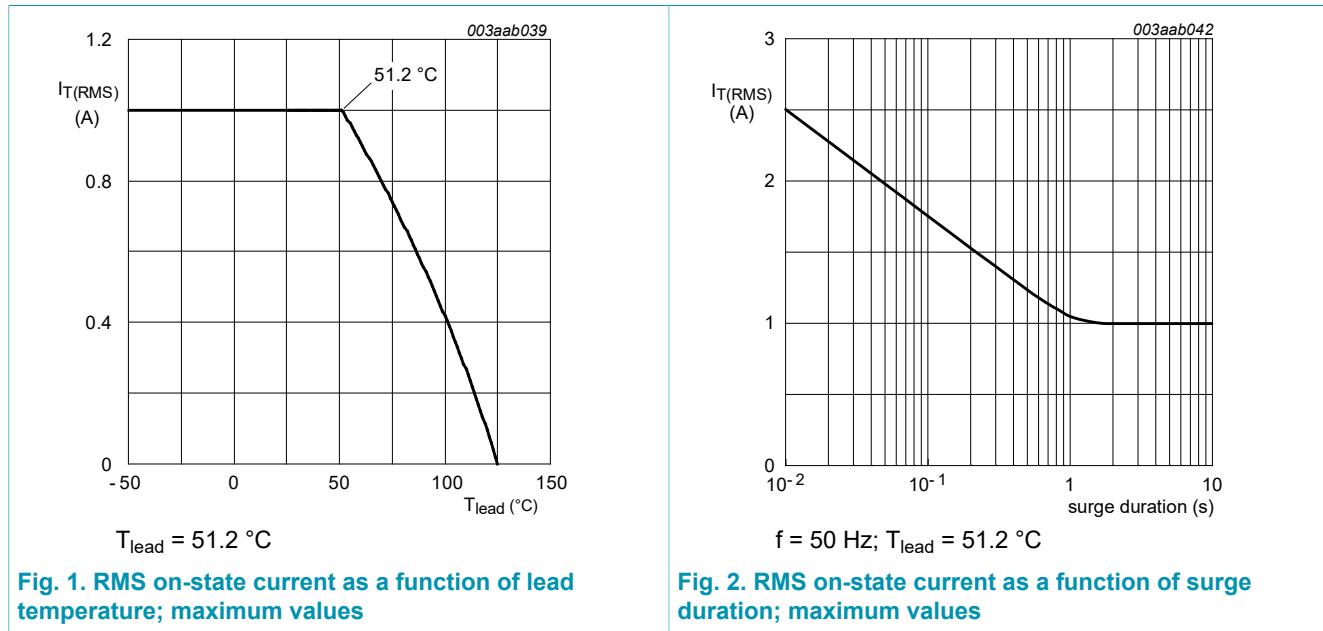
Type number	Package		
	Name	Description	Version
BT131-600D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 51^\circ\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25^\circ\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	12.5	A
		full sine wave; $T_{j(init)} = 25^\circ\text{C}$; $t_p = 16.7\text{ ms}$	-	13.7	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	0.78	A^2s
dI_T/dt	rate of rise of on-state current	$I_G = 10\text{ mA}$	-	50	$\text{A}/\mu\text{s}$
			-	50	$\text{A}/\mu\text{s}$
		$I_G = 14\text{ mA}$	-	10	$\text{A}/\mu\text{s}$
		$I_G = 10\text{ mA}$	-	50	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T_{stg}	storage temperature		-40	150	$^\circ\text{C}$
T_j	junction temperature		-	125	$^\circ\text{C}$



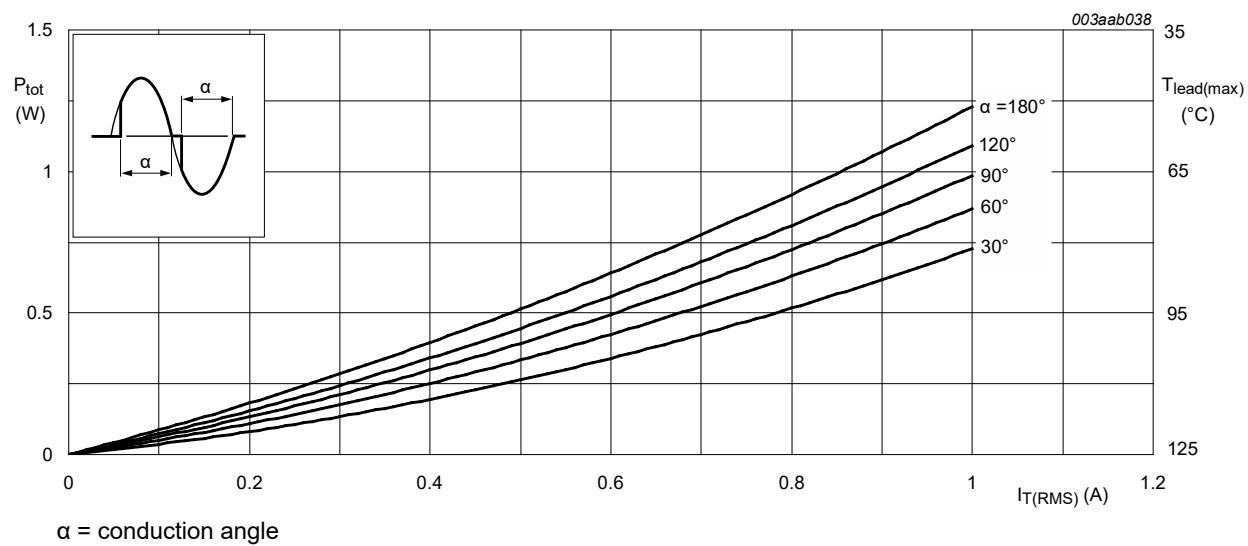


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

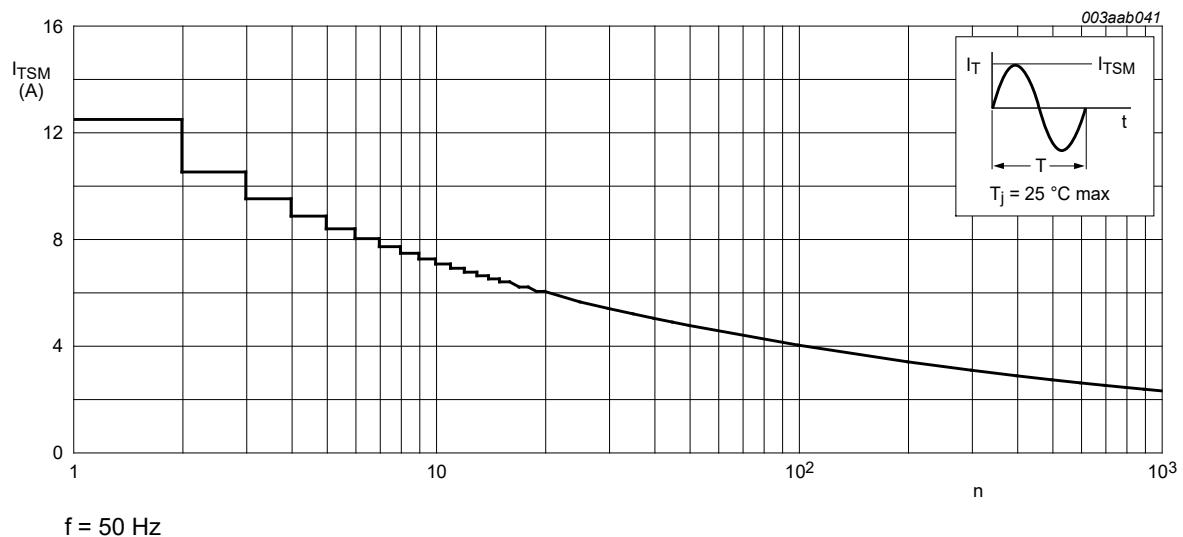
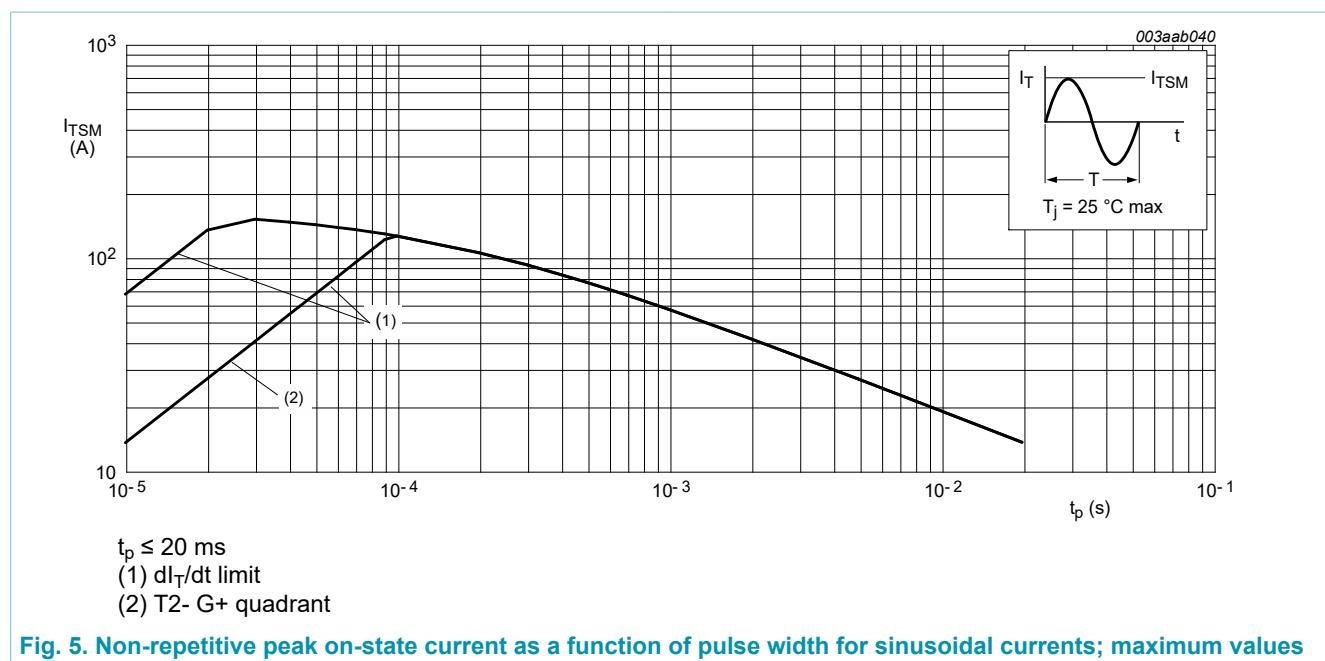


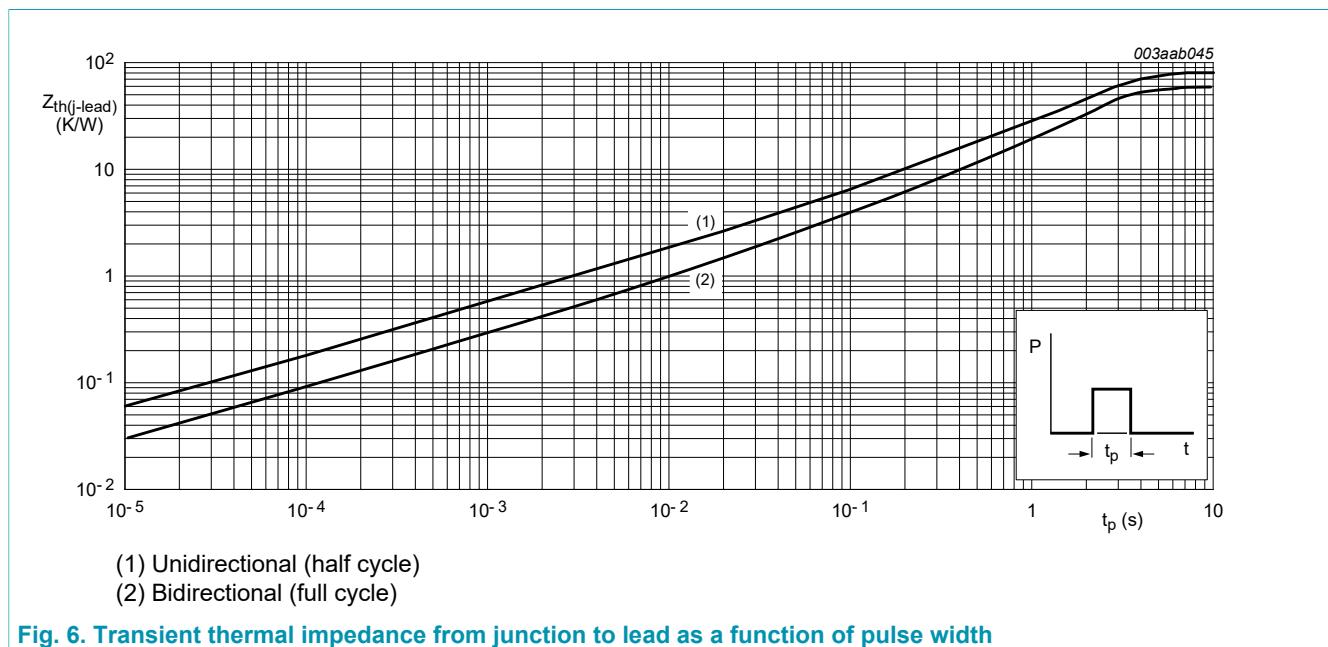
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; Fig. 6	-	-	60	K/W
		half cycle; Fig. 6	-	-	80	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length 4 mm	-	150	-	K/W



9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7		-	-	5	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7		-	-	5	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7		-	-	5	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; Fig. 7		-	-	7	mA
I _L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 8		-	-	10	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 8		-	-	20	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; Fig. 8		-	-	10	mA
		V _D = 12 V; I _G = 0.1 A; T2- G+; T _j = 25 °C; Fig. 8		-	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 9		-	1.3	10	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; Fig. 10		-	1.2	1.5	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11		-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11		0.2	0.3	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C		-	0.1	0.5	mA
Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; R _{GT1(ext)} = 1 kΩ		20	-	-	V/μs
dV _{com} /dt	rate of change of commutating voltage	V _D = 400 V; T _j = 125 °C; dI _{com} /dt = 0.5 A/ms; I _T = 1 A; gate open circuit		3	-	-	V/μs
t _{gt}	gate-controlled turn-on time	I _{TM} = 1.5 A; V _D = 600 V; I _G = 0.1 A; dI _G /dt = 5 A/μs		-	2	-	μs

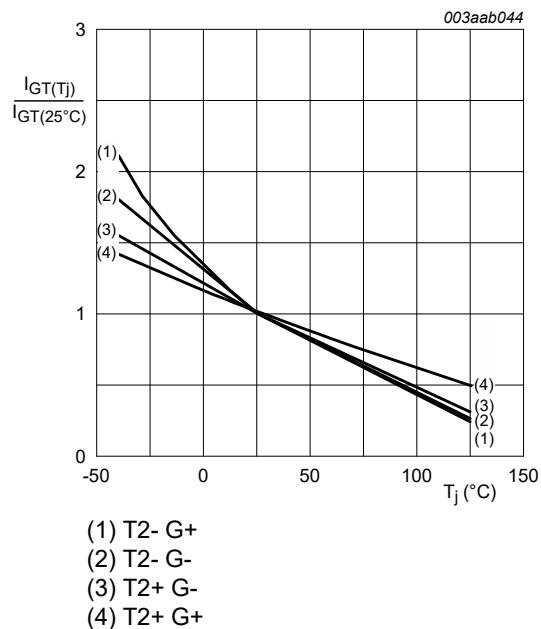


Fig. 7. Normalized gate trigger current as a function of junction temperature

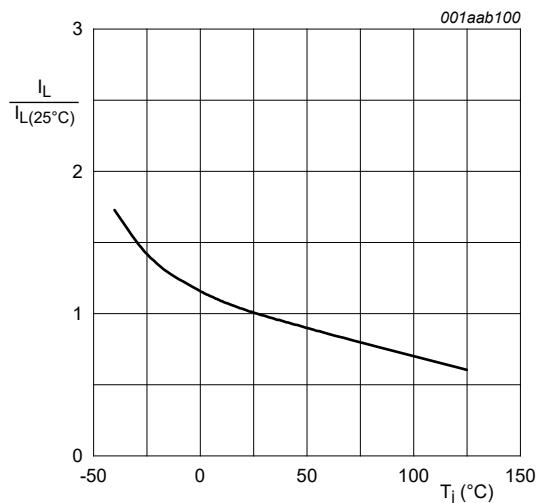


Fig. 8. Normalized latching current as a function of junction temperature

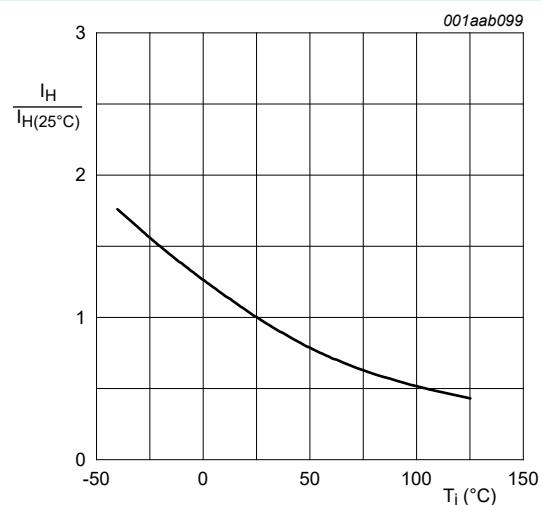


Fig. 9. Normalized holding current as a function of junction temperature

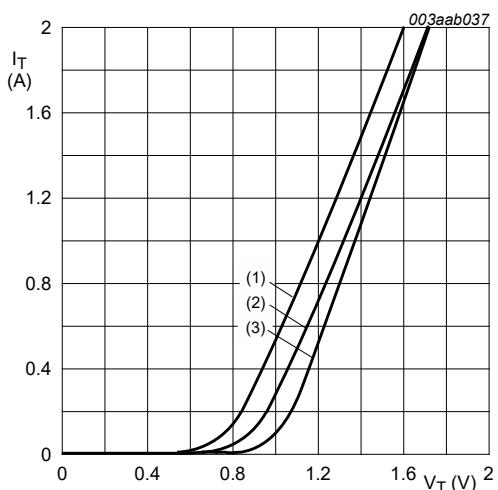


Fig. 10. On-state current as a function of on-state voltage

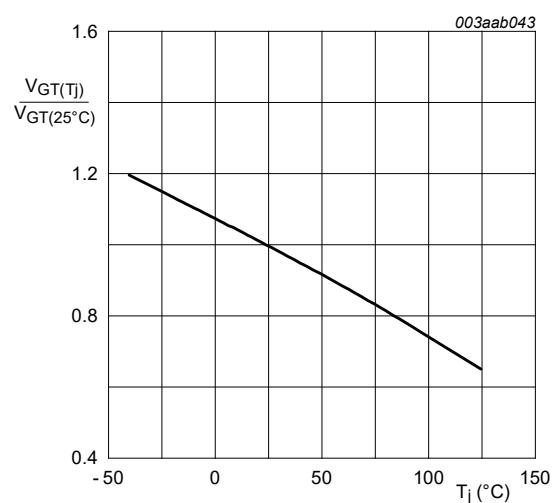
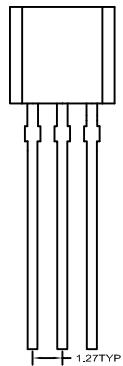


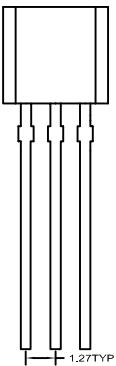
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

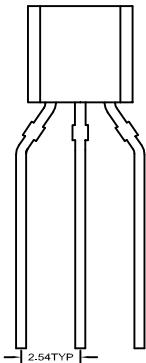
SOT54 PACKAGE OUTLINE



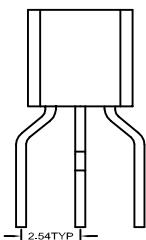
SOT54
Bulk Pack - 412



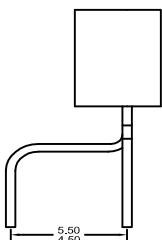
SOT54 LEADS ON CIRCLE
Bulk Pack - 112



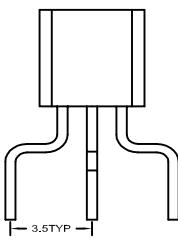
SOT54 WIDE PITCH
Tape/ Reel Pack - 116
Ammo Pack - 126



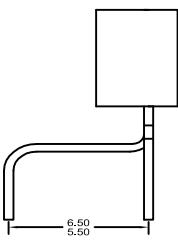
SOT54 LEAD BEND L01
Bulk Pack - 412



6.50
4.50



3.5TYP
SOT54 LEAD BEND L02
Bulk Pack - 412



6.50
5.50

Remark: Detailed dimensions refer to POD drawing.

Fig. 12. Package outline TO-92 (SOT54)

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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